

ABSTRACT

The present disclosure provides a susceptor, a device, and a method for epitaxial growth of a silicon wafer, and an epitaxial silicon wafer, and belongs to the field of semiconductor manufacturing technology. The susceptor for epitaxial growth of the silicon wafer includes: a disc-shaped supporting part configured to support the silicon wafer; an annular periphery extending radially outward from the disc-shaped supporting part, wherein the annular periphery is provided with a plurality of groove regions that is spaced apart from each other and uniformly distributed along a circumferential direction of the annular periphery, each of the groove regions is annular sector-shaped and provided with a plurality of pits arranged in an array.

(Figure 7)